

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.:

10/045,137

Confirmation No.:

3416

First Named Inventor: Wang, Albert Z. H.

Filing Date:

23 October 2001

Group Art Unit:

2811

Examiner:

Hu, S.

Atty. Docket No.:

NS-3868-2C US

Title:

Dual Direction Over-Voltage And Over-Current IC Protection

Device And Its Cell Structure

Assignee(s):

National Semiconductor Corporation

Mountain View, California 10 June 2003

MAIL STOP RCE COMMISSIONER FOR PATENTS PO Box 1450 Alexandria, Virginia 22313-1450

REQUEST FOR CONTINUED EXAMINATION **UNDER 37 CFR 1.114**

Sir:

This is a Request for Continued Examination ("RCE") of the above patent application under 37 CFR 1.114.

Please enter and/or consider the following document which is enclosed or was previously submitted: Amendment, dated 10 June 2003.

The RCE fee required under 37 CFR 1.17(e) is authorized in an accompanying transmittal letter.

Please telephone Attorney for Applicant(s) at 650-964-9767 if there are any auestions.

EXPRESS MAIL LABEL NO.:

ER 070 767 528 US

Respectfully submitted,

Ronald J. Meetin

Attorney for Applicant(s)

Reg. No. 29,089

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Mountain View, CA 94043-4869

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RONALD J. MEETIN Attorney at Law

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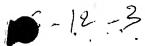
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Appl'n No.: 10/045,137

- 1 -



10 June 2003

STOP RCE MISSIONER FOR PATENTS Box 1450 Alexandria, Virginia 22313-1450

Application No.: 10/045,137

Albert Z.H. Wang

Confirmation No.:

3416

First Inventor: Group Art Unit:

2811

Filing Date:

October 23, 2001

Examiner:

Hu, S.

Atty. Docket No.: NS-3868-2C US

Title:

Dual Direction Over-Voltage And Over-Current IC Protection Device And Its Cell Structure

Assignee:

National Semiconductor Corporation

Sir:

Transmitted herewith are the following documents for the above patent application:

- (1) Return Receipt Postcard;
- (2) This Transmittal Letter (in duplicate);
- (3) RCE (1 pp.);
- (4) Amendment (13 pps.);
- (5) Appendix (4 pps.); and
- (6) Gray ref.

冈 The fee has been calculated as shown below:

CLAIMS AS AMENDED

		Claims Remaining After Amendment		Highest No. Previously Paid For		Present Extra		Rate		Additional Fee
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Total	Claims	25	Minus	20	=	5	х	\$18.00	\$	90.00
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	Total additional fee for this Amendment:							\$	840.00	
\boxtimes	Please charge Deposit Account No. 502641 in the amount of								\$	840.00
\boxtimes	Conditional Petition for Extension of Time: If an extension of time is required, the Commissioner is authorized to deduct the necessary fee from Deposit Account No. 502641.								-	
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EXPRESS MAIL LABEL NO.:

ER 070 767 528 US

Respectfully submitted,

Konald J. Mastin Ronald J. Meetin

Attorney for Applicant(s)

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Assignee(s):

National Semiconductor Corporation

MAIL STOP RCE **COMMISSIONER FOR PATENTS** PO Box 1450 Alexandria, Virginia 22313-1450

AMENDMENT

Responsive to the Office Action mailed 11 March 2003, please amend the above patent application as follows:

IN THE CLAIMS

Amend Claims 2, 3, and 5 - 8 to read:

--2. (Twice amended) The ESD protection structure of Claim 8, wherein said first conductivity type is n-type, and said second conductivity type is p-type.

(Twice amended) The ESD protection structure of Claim 8, wherein said first

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conductivity type is p-type, and said second conductivity type is n-type.

5. (Three times amended) The ESD protection structure of Claim 8, wherein said third semiconductor region includes a well region of said first conductivity type formed in a semiconductor substrate of said second conductivity type.

Appl'n. No.: 10/045,137

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